Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HD313

APPLICATIONS

Low Frequency Power Amplifier.

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature····· −55~150℃

T_j——Junction Temperature····· 150℃

P_C——Collector Dissipation（T_c=25℃）····· 30W

P_C——Collector Dissipation（T_A=25℃）····· 1.75W

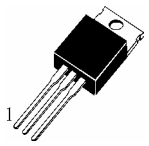
V_{CBO}——Collector-Base Voltage·····60V

V_{CEO}——Collector-Emitter Voltage····· 60V

V_{EBO}——Emitter-Base Voltage····· 5V

I_C——Collector Current····· 3A

TO-220



1－Base，B
2－Collector，C
3－Emitter, E

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CEO}	Collector Cut-off Current			5	mA	V_{CE}=60V, I_B=0
I_{CBO}	Collector Cut-off Current			0.1	mA	V_{CB}=60V, I_E=0
I_{EBO}	Emitter Cut-off Current			1	mA	V_{EB}=4V, I_C=0
H_{FE}（1）	DC Current Gain	60		320		V_{CE}=2V, I_C=1A
H_{FE}（2）	DC Current Gain	60				V_{CE}=2V, I_C=0.1A
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		0.4	1	V	I_C=2A, I_B=0.2A
V_{BE}	Base-Emitter Voltage			1.2	V	V_{CE}=2V, I_C=1A
ft	Current Gain-Bandwidth Product		8		MHz	V_{CE}=5V, I_C=0.5A,
Cob	Output Capacitance		65		pF	V_{CB}=10V, I_E=0， f=1MHz

h_{FE} Classification

D	E	F
60—120	100—200	160—320